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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Application Number	10/763,643
Filing Date	January 23, 2004
Applicant(s)	Yu Min Lin, et al.
Art Unit	2842 2891
Examiner Name	TBD ASOK
Attorney Docket Number	2002-1057 / 24061.69

SHEET 1 OF 1

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Examiner's Initials	Cite No.	Foreign Patent Document (Country Code - Number - Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation Y/N

OTHER PRIOR ART

Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city/country where published
AKS	AP	WORLD WIDE WEB, www.mrs.org/publications/jmr/jmra/2003/jan/009.html, Choi, Kyu-Jeong, et al., "Ultrathin HfO ₂ Gate Dielectric Grown by Plasma-Enhanced Chemical Vapor Deposition Using Hf[OC(CH ₃) ₃] ₄ as a Precursor in the Absence of O ₂ ", printed on March 4, 2003, 1 page.
	AQ	KING, Susan J., "Characterising the Interface Trap Density of Si:P Quantum Computer Devices", School of Electrical Engineering & Telecommunications, 2002, 1 page.
	AR	LIN, Y.S., et al, "Dielectric Property and Thermal Stability of HfO ₂ on Silicon", Applied Physics Letters, Volume 81, Number 11, September 9, 2002, pages 2041-2043.
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Examiner
Signature

Asole Kumar Sarkar

Date
Considered

7/18/05

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